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APPLICATION NO.	FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/693,244	10/693,244 10/24/2003		Takatoshi Tsujimura	CMO.0012US (92096US) 1416	
21906	7590	03/21/2006		EXAMINER	
TROP PRU	NER & F	IU, PC	TUROCY, DAVID P		
8554 KATY	FREEWA	·Υ			
SUITE 100			ART UNIT	PAPER NUMBER	
HOUSTON,	TX 7702	24	1762		

DATE MAILED: 03/21/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

# **Advisory Action**

Application No.	Applicant(s)		
10/693,244	TSUJIMURA ET AL.		
Examiner	Art Unit		
David Turocy	1762		

Before the Filing of an Appeal Brief	Examiner	Art Unit	
i)	David Turocy	1762	
The MAILING DATE of this communication appe	ars on the cover sheet with the c	correspondence add	ress
THE REPLY FILED <u>09 March 2006</u> FAILS TO PLACE THIS AF	PPLICATION IN CONDITION FOR	ALLOWANCE.	
<ol> <li>The reply was filed after a final rejection, but prior to or o this application, applicant must timely file one of the folloplaces the application in condition for allowance; (2) a Notation (3) a Request for Continued Examination (RCE) in comp following time periods:</li> </ol>	n the same day as filing a Notice of pwing replies: (1) an amendment, a otice of Appeal (with appeal fee) in liance with 37 CFR 1.114. The rep	f Appeal. To avoid at ffidavit, or other evid compliance with 37 (	ence, which CFR 41.31; or
a) The period for reply expires months from the mailing of		a final rejection, whichev	oric later to no
b) The period for reply expires on: (1) the mailing date of this Adv event, however, will the statutory period for reply expire later the Examiner Note: If box 1 is checked, check either box (a) or (b) MONTHS OF THE FINAL REJECTION. See MPEP 706.07(f	an SIX MONTHS from the mailing date o . ONLY CHECK BOX (b) WHEN THE F	f the final rejection.	
Extensions of time may be obtained under 37 CFR 1.136(a). The date on been filed is the date for purposes of determining the period of extension a CFR 1.17(a) is calculated from: (1) the expiration date of the shortened stabove, if checked. Any reply received by the Office later than three month earned patent term adjustment. See 37 CFR 1.704(b).  NOTICE OF APPEAL	which the petition under 37 CFR 1.136(a and the corresponding amount of the fee, atutory period for reply originally set in the	The appropriate extension of (2)	on fee under 37 as set forth in (b)
<ol> <li>The Notice of Appeal was filed on A brief in com of filing the Notice of Appeal (37 CFR 41.37(a)), or any e Since a Notice of Appeal has been filed, any reply must</li> </ol>	extension thereof (37 CFR 41.37(e)	), to avoid dismissal	of the appeal.
AMENDMENTS	·	·	
<ol> <li>The proposed amendment(s) filed after a final rejection,</li> <li>(a) They raise new issues that would require further co</li> <li>(b) They raise the issue of new matter (see NOTE below.</li> </ol>	onsideration and/or search (see NC		because
(c) ☐ They are not deemed to place the application in be appeal; and/or	tter form for appeal by materially r	educing or simplifying	g the issues for
(d) They present additional claims without canceling a NOTE: (See 37 CFR 1.116 and 41.33(a))		ejected claims.	•
4. The amendments are not in compliance with 37 CFR 1.		ompliant Amendmen	t (PTOL-324).
5. $\square$ Applicant's reply has overcome the following rejection(s	s):	•	
<ol> <li>Newly proposed or amended claim(s) would be a the non-allowable claim(s).</li> </ol>	allowable if submitted in a separate	e, timely filed amendr	nent canceling
7. For purposes of appeal, the proposed amendment(s): a) how the new or amended claims would be rejected is pro The status of the claim(s) is (or will be) as follows:	Will not be entered, or b)  vovided below or appended.	vill be entered and an	explanation of
Claim(s) allowed: _Claim(s) objected to:		•	
Claim(s) rejected: <u>1-18 and 26-30</u> . Claim(s) withdrawn from consideration:			• •
AFFIDAVIT OR OTHER EVIDENCE			
<ol> <li>The affidavit or other evidence filed after a final action, because applicant failed to provide a showing of good at and was not earlier presented. See 37 CFR 1.116(e).</li> </ol>	nd sufficient reasons why the affida	avit or other evidence	is necessary
<ol> <li>The affidavit or other evidence filed after the date of filing entered because the affidavit or other evidence failed to showing a good and sufficient reasons why it is necessa</li> </ol>	overcome <u>all</u> rejections under apperty and was not earlier presented.	eal and/or appellant f See 37 CFR 41.33(d)	ails to provide a (1).
10.  ☐ The affidavit or other evidence is entered. An explanation REQUEST FOR RECONSIDERATION/OTHER	on of the status of the claims after	entry is below or atta	ched.
11.  The request for reconsideration has been considered b See Detailed Action.			ance because:
<ul><li>12. ☐ Note the attached Information Disclosure Statement(s)</li><li>13. ☐ Other:</li></ul>	. (PTO/SB/08 or PTO-1449) Paper	No(s)	
	•		
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#### **DETAILED ACTION**

#### Response to Amendment

1. The applicant's amendments, filed 3/9/2006, have been amended to include new limitations that were not present in the finally rejected claims and therefore would clearly require further search and/or consideration. Therefore the examiner has not entered the amendments.

### Response to Arguments

2. Applicant's arguments filed 3/9/2006 have been fully considered but they are not persuasive.

The applicants have argued against the 35 USC 112 1<sup>st</sup> paragraph rejection regarding scope of enablement, stating the examiner has not established that a person skilled in the art could not use the genus as a whole without undue experimentation. The examiner respectfully disagrees and maintains the position that while the specification clearly enables one of ordinary skill in the art that a first gas of SiH<sub>4</sub> and a second gas of H<sub>2</sub> using the process as claimed will result in depositing a microcrystalline film during the second process. The specification does not provide additional direction or working examples to one of ordinary skill in the art to provide any combination of various gases, each of which is within the scope of the claimed invention, to deposit a microcrystalline film during the second process without undue experimentation in determining which combination of the two gases selected from the entire genus of gases, supplied in the method as claimed, will result in depositing a

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microcrystalline thin film in the second process. The breadth of the claim clearly encompasses all gases, but the specification does not give direction, other then a first gas of SiH<sub>4</sub> and a second gas of H<sub>2</sub>, to provide a microcrystalline thin film in a second process and therefore one ordinary skill in the art would be required to do undue experimentation to determine which combinations of gases result in a microcrystalline thin film.

As for the 35 USC 112 1<sup>st</sup> paragraph rejection of claims 26-28, the examiner maintains the above as well as maintains that the specification does not provide additional direction or working examples to one of ordinary skill in the art to provide any combination of various gases at any of a multitude of flow rates, each of which is within the scope of the claimed invention, to supply a flow rate ratio to prevent an amorphous film deposition.

The examiner notes the use of the generic first gas and second gas in the specification; however, such a broad disclosure does not provide enablement for the entire genus of first and second gases to deposit a microcrystalline thin film in a second process as presently claimed.

The applicants have argued against the Nakata '349, stating the reference clearly discloses depositing amorphous silicon during the first process and does not disclose the microcrystalline thin film in the second process. In addition the applicant has argued against the combination of Nakata '349 with Nakata '062 stating that there is no motivation to modify '349 with '062. While the examiner agrees Nakata '349 discloses depositing an amorphous silicon during the first process, however, the examiner notes

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the claim as written does not require there to be no amorphous deposition during the

- first process. Additionally the examiner notes the process as taught by Nakata '349 does not teach of depositing a microcrystalline thin film in the second step, it is the examiners position that after stopping the flow of SiH<sub>4</sub>, the process of Nakata '349 inherently results in at least a quantitative amount of continual deposition, during the
- second step, at which H<sub>2</sub> is maintained at a constant rate, due to the presence of SiH<sub>4</sub> and H<sub>2</sub> remaining in the process chamber. In addition, residual SiH<sub>4</sub> remaining in the process chamber with the constant flow of H<sub>2</sub> will result in a H<sub>2</sub> to SiH<sub>4</sub> dilution ratio to deposit a quantitative amount of microcrystalline thin film directly from the vapor phase,
- See Nakata '062 which discloses adjusting the hydrogen dilution ratio to deposit microcrystalline thin films directly from vapor phase (Column 5, lines 20-25). Therefore the examiner has not modified Nakata '349 with Nakata '062, but rather has supplied Nakata '062 as a showing that the certain H<sub>2</sub> to SiH<sub>4</sub> dilution ratio results in a
  - microcrystalline thin film. In addition, the examiner has noted stopping the flow of SiH<sub>4</sub> with continual H<sub>2</sub> flow, will in time result in a dilution ratio, due to the residual SiH<sub>4</sub> remaining in the chamber, as described by Nakata '062 and result in a quantitative amount of microcrystalline thin film directly from the vapor phase.
  - The applicant has argued against the examiners combination of Nakata '349 with the admitted state of the art on page 3 of the specification, stating there is no motivation to combine the reference with the background as supplied by the applicant. The examiner notes however, that the examiner has not modified Nakata '349 with the admitted state of the art, but rather has supplied the admitted state of the art as a

showing that applying a high-energy electric field to the SiH<sub>4</sub> results in breaking the SiH<sub>4</sub> down into a more reactive SiH<sub>2</sub>.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to David Turocy whose telephone number is (571) 272-2940. The examiner can normally be reached on Monday-Friday 8:30-6:00, No 2nd Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Timothy Meeks can be reached on (571) 272-1423. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR.

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- Business Center (EBC) at 866-217-9197 (toll-free).

David Turocy AU 1762 TIMOTHY MEEKS

OUDERVISORY PATENT EXAMINER